

## Description

The DMG6968UDM uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 20V, I_{D} = 7A$ 

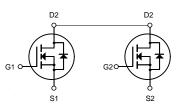
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 4.5V$ 

#### Application

Battery protection Load switch Power management



SOT-23-6L



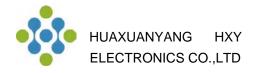
**Dual N-Channel MOSFET** 

#### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMG6968UDM	SOT-23-6L	HXY MOSFET	3000

#### Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	ate-Source Voltage <u>+</u> 10	
I <sub>D</sub> @T <sub>A</sub> =25℃	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	7	А
Ідм	Pulsed Drain Current <sup>1</sup>	25	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	1.25	W
Тята	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient <sup>3</sup>	100	°C/W

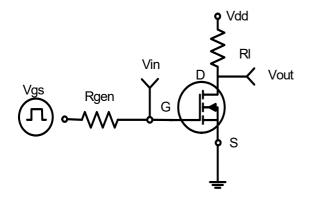


### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

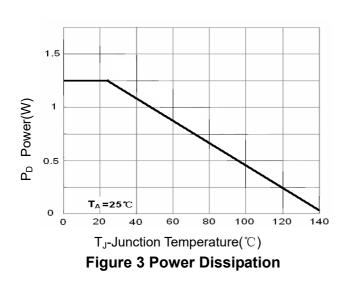
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	-	14	20	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.5A	-	19	25	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =4.5A	-	10	-	S
Dynamic Characteristics						
Input Capacitance	Cliss		-	900	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V, F=1.0MHz	-	220	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F = 1.0101112	-	100	-	PF
Switching Characteristics		·				
Turn-on Delay Time	t <sub>d(on)</sub>		-	10	20	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V,I <sub>D</sub> =1A	-	11	25	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4.5V, $R_{GEN}$ =6 $\Omega$	-	35	70	nS
Turn-Off Fall Time	t <sub>f</sub>		-	30	60	nS
Total Gate Charge	Qg		-	12	15	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =6A, V <sub>GS</sub> =4.5V	-	2.3	-	nC
Gate-Drain Charge	$Q_gd$	• • • • • • • • • • • • • • • • • • •	-	1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.5	А

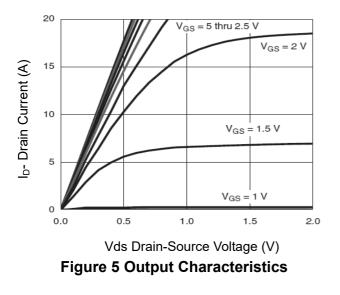


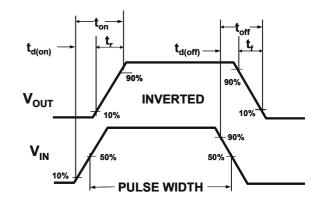
## **Typical Electrical and Thermal Characteristics**



## Figure 1:Switching Test Circuit







#### Figure 2:Switching Waveforms

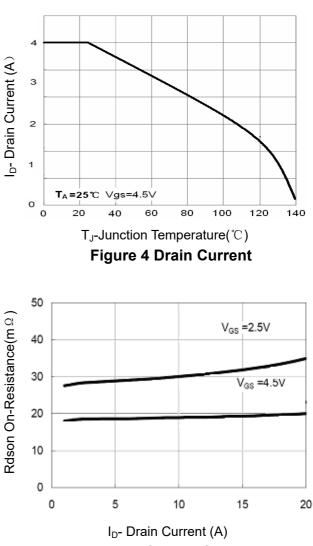
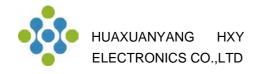
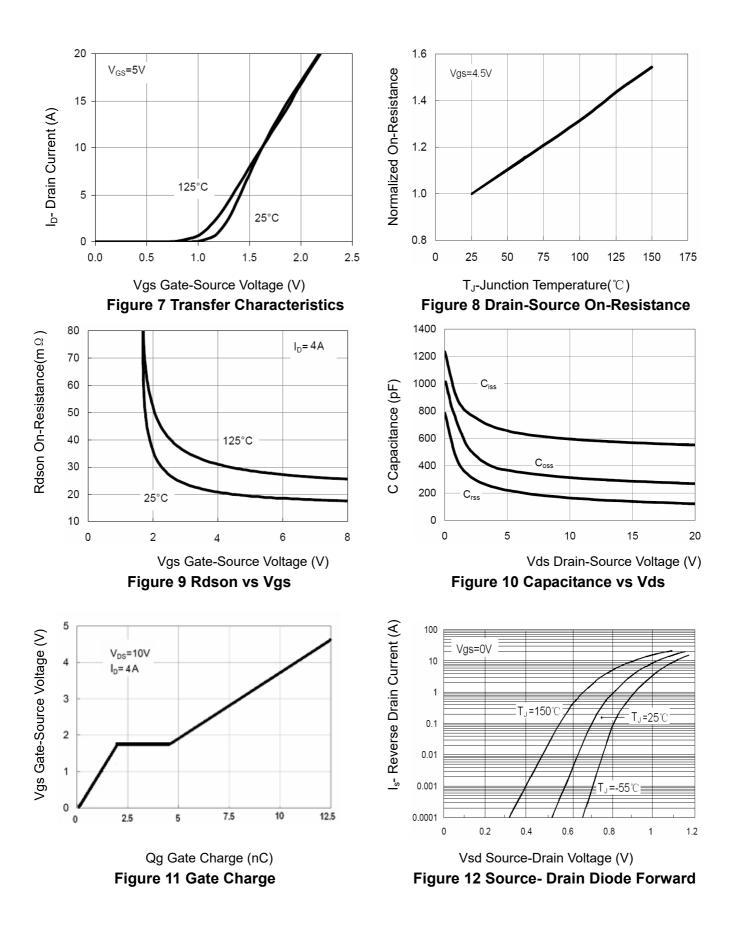
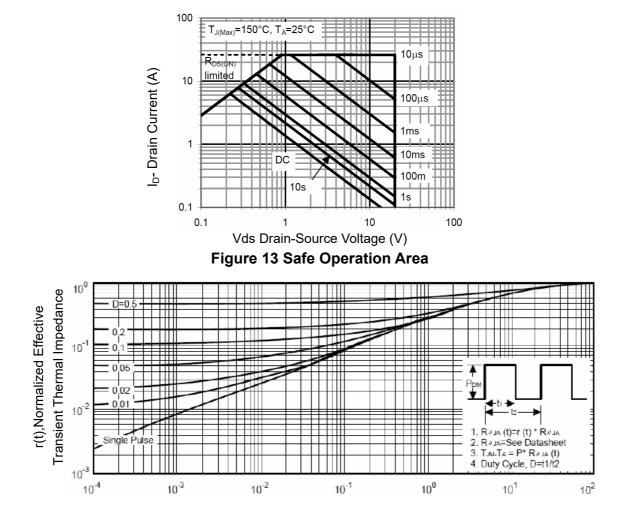


Figure 6 Drain-Source On-Resistance





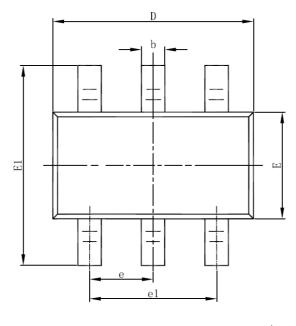


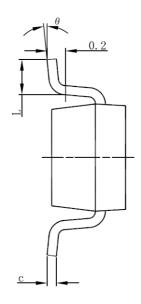


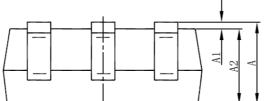
Square Wave Pluse Duration(sec) Figure 14 Normalized Maximum Transient Thermal Impedance



## SOT-23-6L Package Information







Sumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
e	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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